

SILICON DIODE CHIPS

DEVICE NO. : SD-0011

1. Scope :

This specification applies to silicon PIN diode chips,
Device NO. SD-0011

2. Structure :

- 2-1. Planar type : Silicon Diode
- 2-2. Electrodes :
 - Top side (Anode) : Aluminum Alloy .
 - Back side (Cathode) : Gold Alloy.

3. Size :

- 3-1. Chip size : 11.8 mils x 11.8 mils (0.300 mm x 0.300 mm).
- 3-2. Chip thickness : 7.5 ± 1.2 mils (0.190 ± 0.3 mm).
- 3-3. Active area : 6.3 mils x 6.3 mils (0.16 mm x 0.16 mm).
- 3-4. Bonding pad (Anode) : 6.3 mils x 6.3 mils (0.16mm x 0.16 mm) .
- 3-5. Pattern drawing : Refer to the attached drawing.

4. Electrical characteristics (Ta = 25)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse dark current	I_D	$V_R=20V$ $H=0mW/cm^2$		0.3		nA
Reverse breakdown voltage	$V_{(BR)R}$	$I_R=100\mu A$ $H=0mW/cm^2$	60			V
Forward Voltage	V_F	$I_F=20mA$		0.8	1.2	V
Capacitance	C_t	$V_R=5V$ $f=1MHz$		0.36		pF

